

Mj Deen

List of Publications by Year in descending order

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16
papers

1,112
citations

759233

12
h-index

1125743

13
g-index

16
all docs

16
docs citations

16
times ranked

640
citing authors

#	ARTICLE	IF	CITATIONS
1	A review of gate tunneling current in MOS devices. <i>Microelectronics Reliability</i> , 2006, 46, 1939-1956.	1.7	150
2	Channel noise modeling of deep submicron MOSFETs. <i>IEEE Transactions on Electron Devices</i> , 2002, 49, 1484-1487.	3.0	133
3	MOSFET Modeling for RF IC Design. <i>IEEE Transactions on Electron Devices</i> , 2005, 52, 1286-1303.	3.0	128
4	A general noise and S-parameter deembedding procedure for on-wafer high-frequency noise measurements of MOSFETs. <i>IEEE Transactions on Microwave Theory and Techniques</i> , 2001, 49, 1004-1005.	4.6	105
5	High-Frequency Noise of Modern MOSFETs: Compact Modeling and Measurement Issues. <i>IEEE Transactions on Electron Devices</i> , 2006, 53, 2062-2081.	3.0	104
6	High frequency noise of MOSFETs I Modeling. <i>Solid-State Electronics</i> , 1998, 42, 2069-2081.	1.4	99
7	Extraction of the induced gate noise, channel noise, and their correlation in submicron MOSFETs from RF noise measurements. <i>IEEE Transactions on Electron Devices</i> , 2001, 48, 2884-2892.	3.0	99
8	Compact-Modeling Solutions For Nanoscale Double-Gate and Gate-All-Around MOSFETs. <i>IEEE Transactions on Electron Devices</i> , 2006, 53, 2128-2142.	3.0	91
9	High-frequency small signal AC and noise modeling of MOSFETs for RF IC design. <i>IEEE Transactions on Electron Devices</i> , 2002, 49, 400-408.	3.0	68
10	Effects of hot-carrier stress on the performance of the lc-tank cmos oscillators. <i>IEEE Transactions on Electron Devices</i> , 2003, 50, 1334-1339.	3.0	48
11	A 4-mW monolithic CMOS LNA at 5.7GHz with the gate resistance used for input matching. <i>IEEE Microwave and Wireless Components Letters</i> , 2006, 16, 188-190.	3.2	43
12	MOSFET modeling for low noise, RF circuit design. , 0, , .		21
13	A New Method for the Channel-Length Extraction in MOSFETs With Sub-2-nm Gate Oxide. <i>IEEE Electron Device Letters</i> , 2004, 25, 202-204.	3.9	12
14	Towards an optimal MIIM diode for rectennas at 10.6 $\hat{\mu}$ m. <i>Results in Materials</i> , 2021, 11, 100204.	1.8	9
15	Analytical modeling of MOSFET noise parameters for analog and RF applications. , 0, , .		1
16	Towards low-cost, high-sensitivity, integrated biosensors. , 2008, , .		1